

정오 "반도체 제조 이온주입 공정의 이온 임플란타 장치에서 엑스레이 발생 특성"

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Erratum to "Characterization of X-ray Emitted in the Ion Implantation Process of Semiconductor Operations"

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한국산업보건학회 편집위원회는 본 논문의 일부 내용(Figure 2)에 대해 저자들의 변경 신청을 접수 받았습니다. 이에 편집위원회는 변경 신청 사항을 검토하여, "정오표(Erratum)" 제시로 최종 결정하였습니다.

Erratum : 반도체 제조 이온주입 공정의 이온 임플란타 장치에서 엑스레이 발생 특성, 한국산업보건학회지, 제33권 제4호(2023) 중 그림(Figure) 2를 그림 내용을 더 분명하게 나타내 독자 이해를 더 쉽게 하기 위해 교체합니다.

수정 전



Figure 2. Three points where X-ray was monitored in ion implantation process (beam line, panel behind high voltage electric system, and ion source chamber)

수정 후

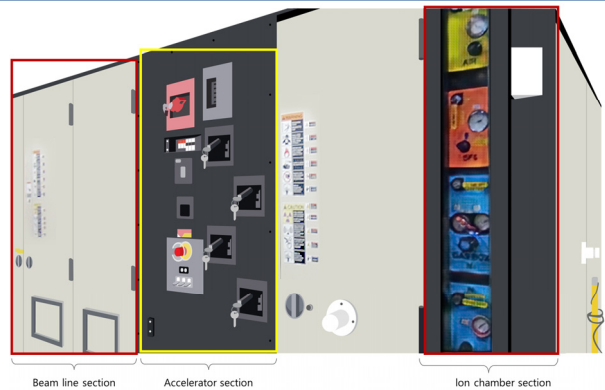


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